

N-channel TrenchMOS logic level FET Rev. 02 — 26 April 2011

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

AEC Q101 compliant

Low conduction losses due to low on-state resistance

1.3 Applications

Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	T _{mb} = 25 °C	-	-	11	А
P _{tot}	total power dissipation		-	-	54	W
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 5 A; T _j = 25 °C	-	152	173	mΩ
		$V_{GS} = 5 \text{ V}; \text{ I}_{D} = 5 \text{ A}; \text{ T}_{j} = 25 ^{\circ}\text{C}$	-	165	180	mΩ
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 5.5 \text{ A}; \text{V}_{\text{sup}} \leq 25 \text{ V}; \\ R_{\text{GS}} &= 50 \Omega; \text{V}_{\text{GS}} = 5 \text{ V}; \\ T_{j(\text{init})} &= 25 ^{\circ}\text{C}; \text{ unclamped} \end{split}$	-	-	1.5	mJ

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

SOT404 (D2PAK)

3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK96180-100A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

4. Limiting values

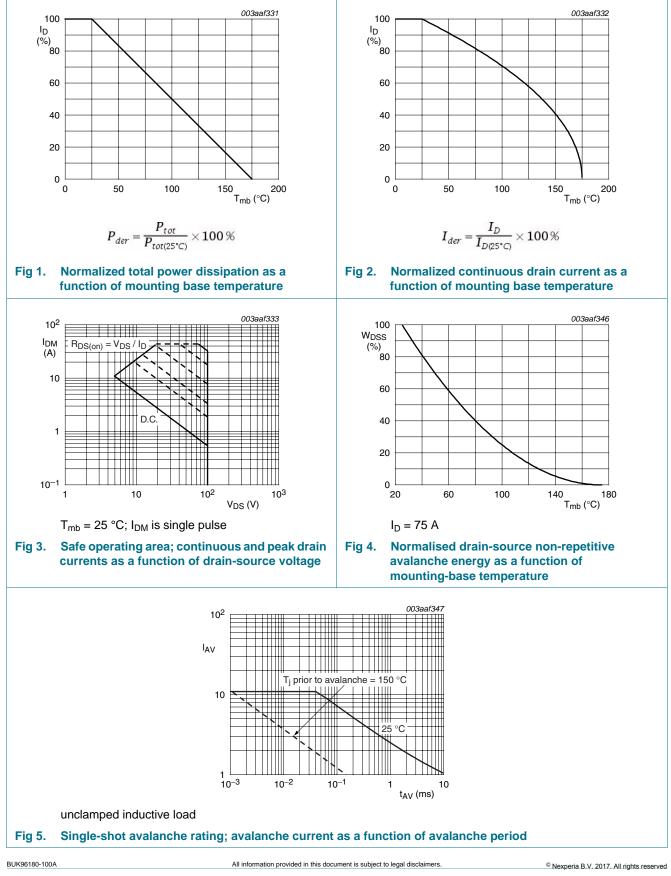
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	100	V
V _{GS}	gate-source voltage		-15	15	V
I _D	drain current	T _{mb} = 25 °C	-	11	А
		$T_{mb} = 100 \ ^{\circ}C$	-	7.7	А
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed	-	44	А
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	54	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
I _S	source current	T _{mb} = 25 °C	-	11	А
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	44	А
Avalanche ru	ggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 5.5 A; $V_{sup} \le 25$ V; R_{GS} = 50 Ω ; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped	-	1.5	mJ

BUK96180-100A

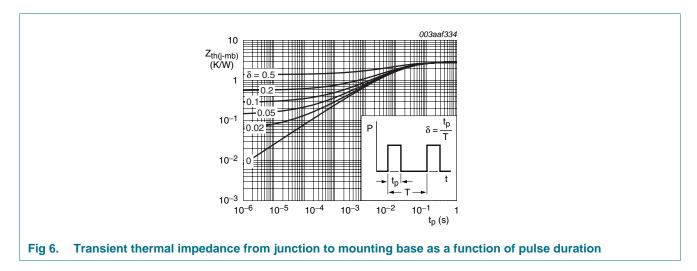
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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base		-	-	2.8	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; FR4 board	-	50	-	K/W



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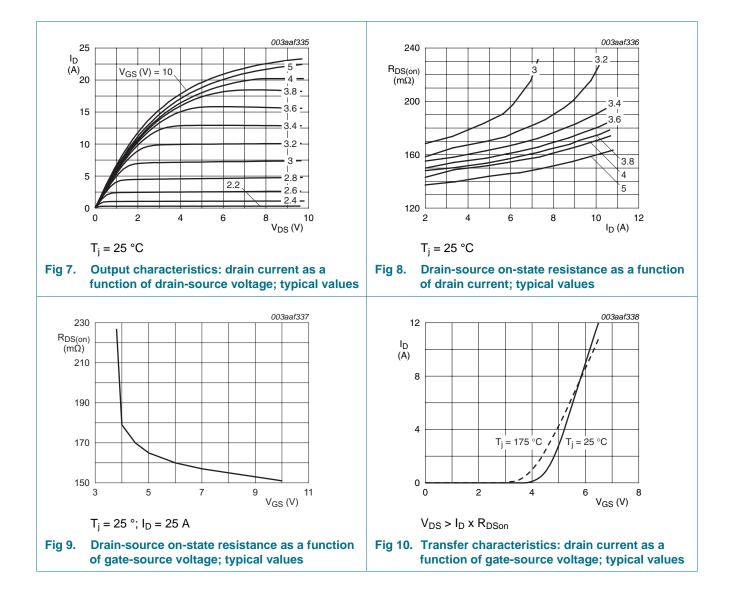
Characteristics 6.

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	V	
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
V _{GS(th)}	gate-source threshold	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C	-	-	2.3	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	0.5	-	-	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
I _{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 5 \text{ V}; \text{ I}_{D} = 5 \text{ A}; \text{ T}_{j} = 175 \text{ °C}$	-	-	450	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}$	-	170	200	mΩ
		V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C	-	152	173	mΩ
		V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C	-	165	180	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	464	619	pF
C _{oss}	output capacitance	T _j = 25 °C	-	60	72	pF
C _{rss}	reverse transfer capacitance		-	37	50	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	9	20	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 \text{ °C}$	-	112	157	ns
t _{d(off)}	turn-off delay time		-	18	27	ns
t _f	fall time		-	25	38	ns
L _D	internal drain inductance	measured from drain lead 6 mm from package to centre of die	-	4.5	-	nH
		measured from upper edge of drain tab to centre of die	-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad	-	7.5	-	nH
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_{S} = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$	-	0.85	1.2	V
		I _S = 11 A; V _{GS} = 0 V; T _j = 25 °C	-	1.1	-	V
t _{rr}	reverse recovery time	I _S = 11 A; dI _S /dt = -100 A/μs;	-	49	-	ns
Q _r	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	0.13	-	μC

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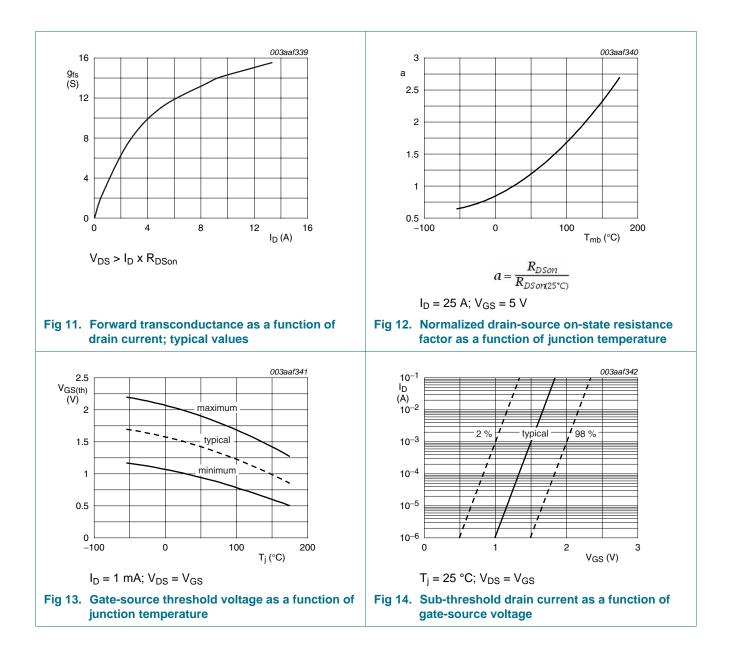
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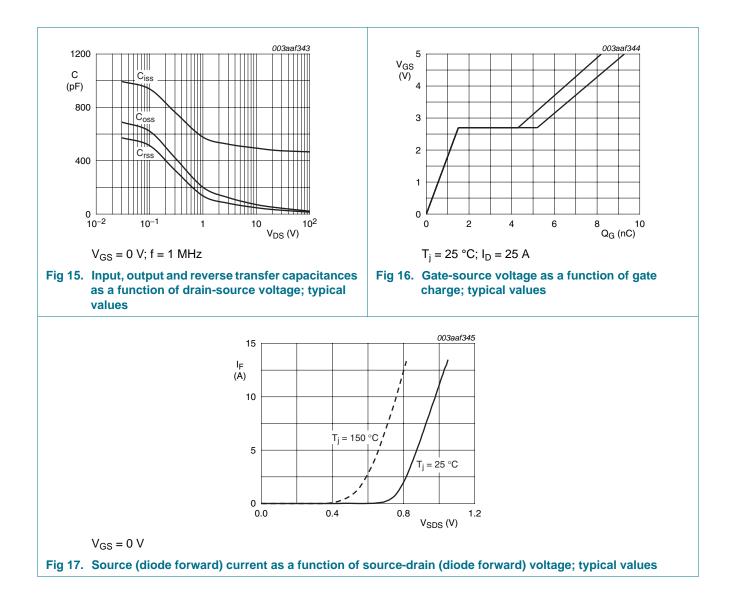
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7. Package outline

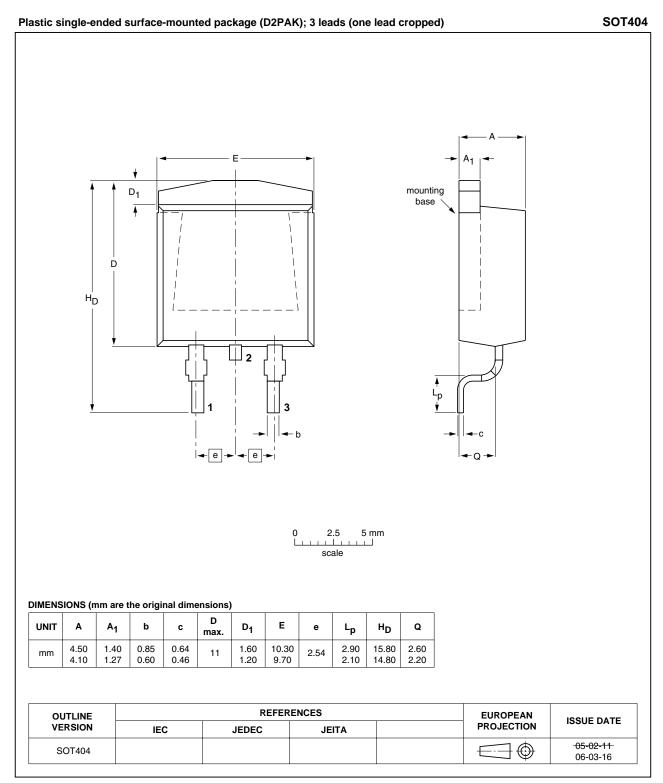


Fig 18. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7.	Revision history					
Document	ID	Release date	Data sheet status	Change notice	Supersedes	
BUK96180	-100A v.2	20110426	Product data sheet	-	BUK95180_96180-100A v.1	
Modifications:		 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 				
		 Legal texts have 	ave been adapted to the r	new company name	where appropriate.	
		 Type number 	BUK96180-100A separa	ted from data sheet	BUK95180_96180-100A v.1.	
BUK95180	_96180-100A v.1	20000501	Product specification	-	-	

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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